

**Description**

The SX20N02DF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = 20V$   $I_D = 20A$

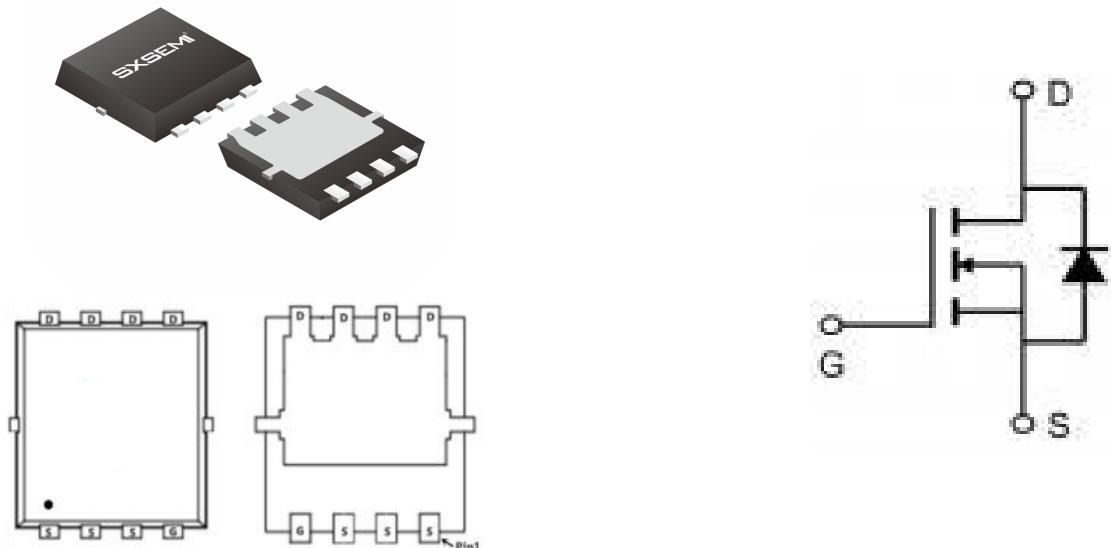
$R_{DS(ON)} < 8.0m\Omega$  @  $V_{GS}=10V$

**Application**

Battery protection

Load switch

Uninterruptible power supply

**PDFN3\*3-8L****Absolute Maximum Ratings (TC=25°C unless otherwise noted)**

Symbol	Parameter	Max.	Units
$V_{DSS}$	Drain-Source Voltage	20	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Continuous Drain Current $T_C = 25^\circ C$	20	A
$I_D$	Continuous Drain Current $T_C = 100^\circ C$	15	A
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>	60	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>note2</sup>	36	mJ
$P_D$	Power Dissipation $T_C = 25^\circ C$	31	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.84	$^\circ C/W$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ C$

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$	20	22	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=20\text{V}$ , $V_{GS}=0\text{V}$ ,	-	-	1.0	$\mu\text{A}$
IGSS	Gate to Body Leakage Current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 12\text{V}$	-	-	$\pm 100$	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.4	0.7	1.1	V
RDS(on)	Static Drain-Source on-Resistance note3	$V_{GS}=4.5\text{V}$ , $I_D=25\text{A}$	-	6.1	8.0	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_D=10\text{A}$	-	8.8	13	
Ciss	Input Capacitance	$V_{DS}=10\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	1458	-	pF
Coss	Output Capacitance		-	238	-	pF
Crss	Reverse Transfer Capacitance		-	212	-	pF
Qg	Total Gate Charge	$V_{DS}=10\text{V}$ , $I_D=25\text{A}$ , $V_{GS}=4.5\text{V}$	-	19	-	nC
Qgs	Gate-Source Charge		-	3	-	nC
Qgd	Gate-Drain("Miller") Charge		-	6.4	-	nC
td(on)	Turn-on Delay Time	$V_{DS}=10\text{V}$ , $I_D=10\text{A}$ , $R_{GEN}=3\Omega$ , $V_{GS}=4.5\text{V}$	-	10	-	ns
tr	Turn-on Rise Time		-	21	-	ns
td(off)	Turn-off Delay Time		-	39	-	ns
tf	Turn-off Fall Time		-	19	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current	-	-	50	A	
ISM	Maximum Pulsed Drain to Source Diode Forward Current	-	-	200	A	
VSD	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$ , $I_S=30\text{A}$	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	IF=20A, $dI/dt=100\text{A}/\mu\text{s}$	-	25	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	20	-	nC

**Note :**

- 1、The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The EAS condition:  $T_J=25^\circ\text{C}$ ,  $V_{DD}=16\text{V}$ ,  $V_G=10\text{V}$ ,  $R_G=0.6\Omega$ ,  $L=0.5\text{mH}$ ,  $I_{AS}=33\text{A}$
- 4、The power dissipation is limited by  $175^\circ\text{C}$  junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

## Typical Characteristics

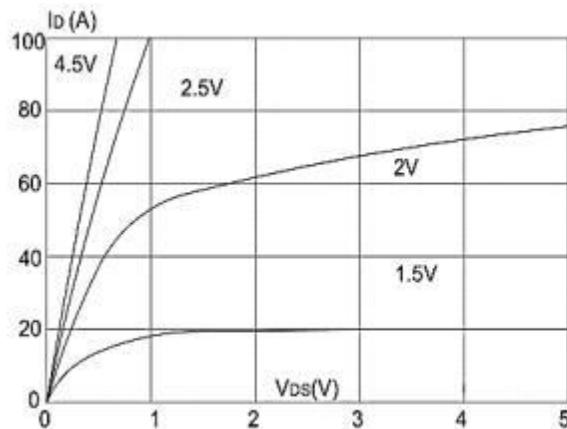


Figure 1: Output Characteristics

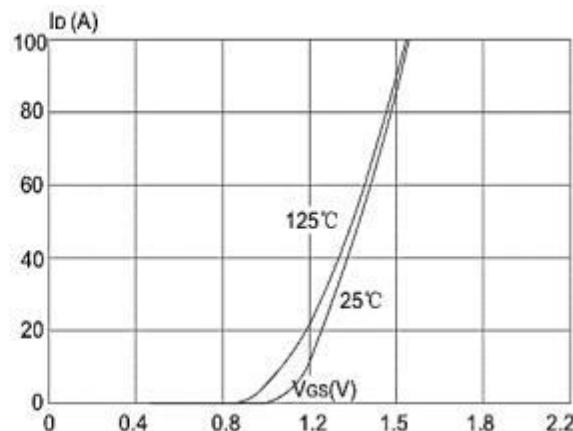


Figure 2: Typical Transfer Characteristics

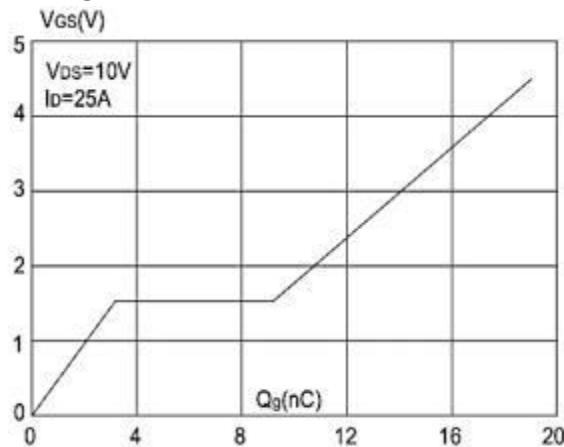


Figure 3: On-resistance vs. Drain Current

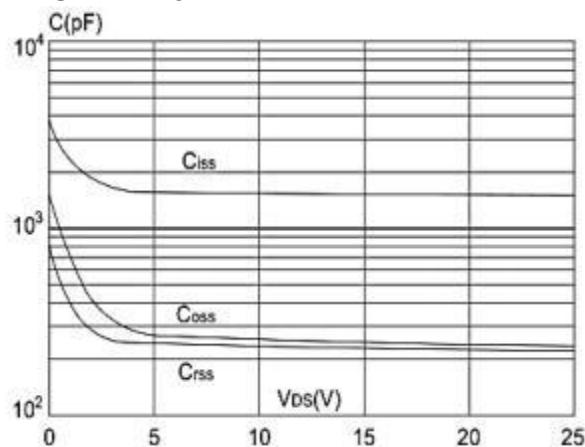


Figure 4: Body Diode Characteristics

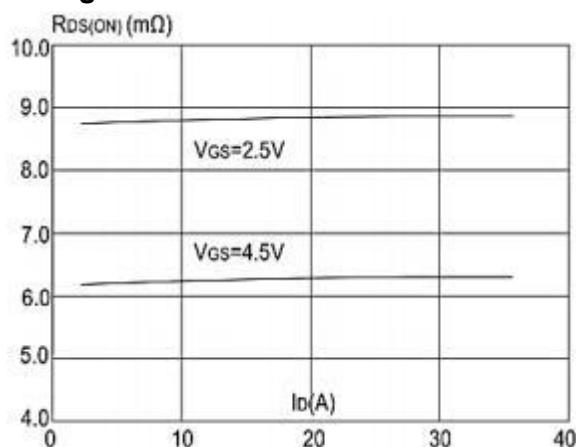


Figure 5: Gate Charge Characteristics

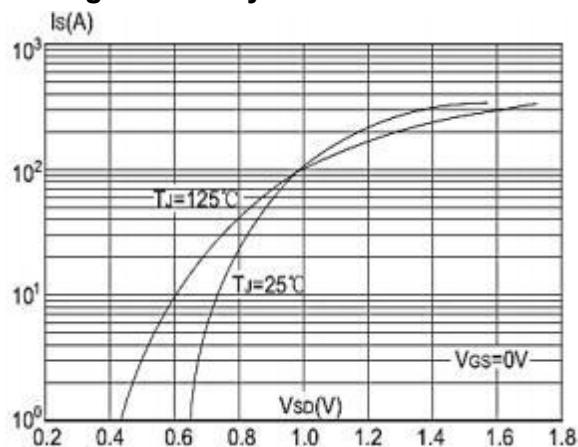


Figure 6: Capacitance Characteristics

## Typical Characteristics

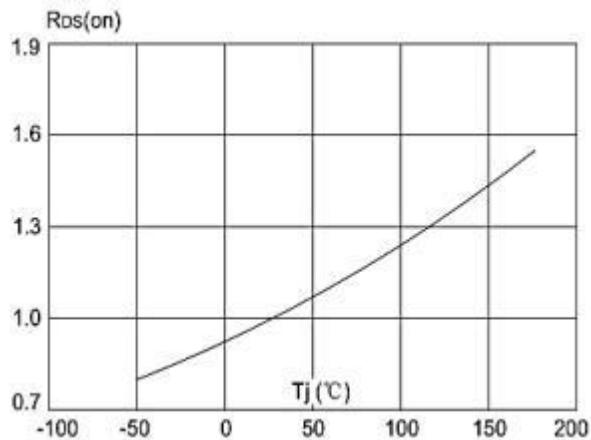
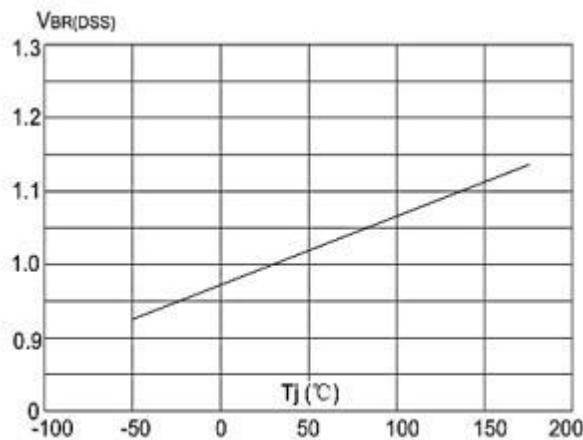


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

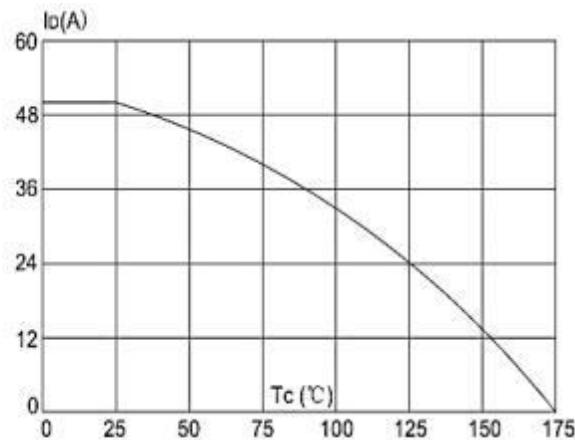
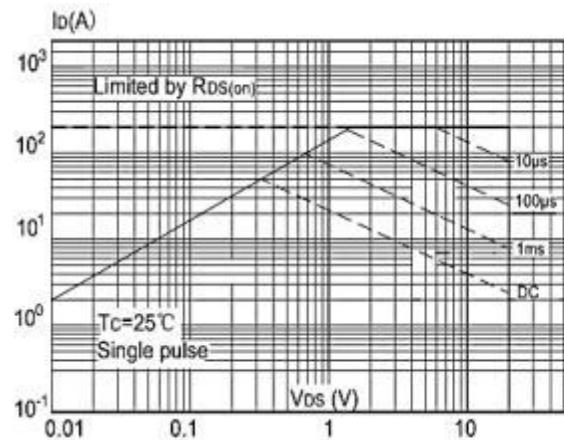


Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

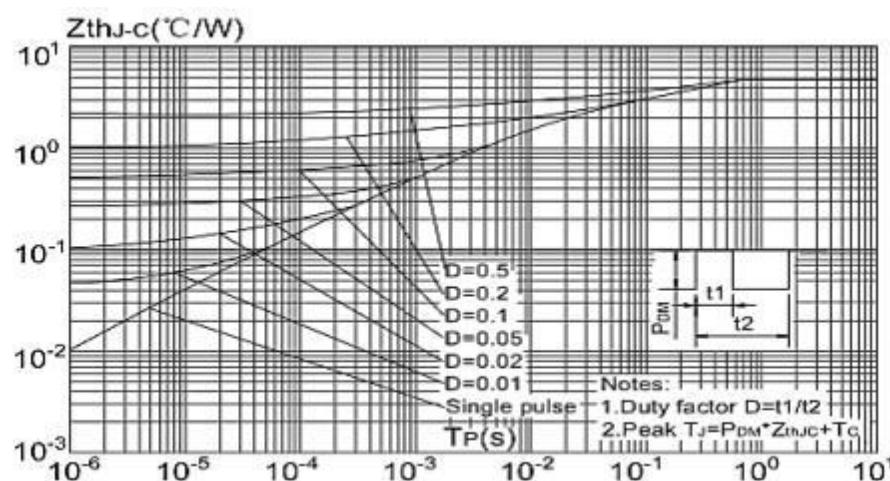
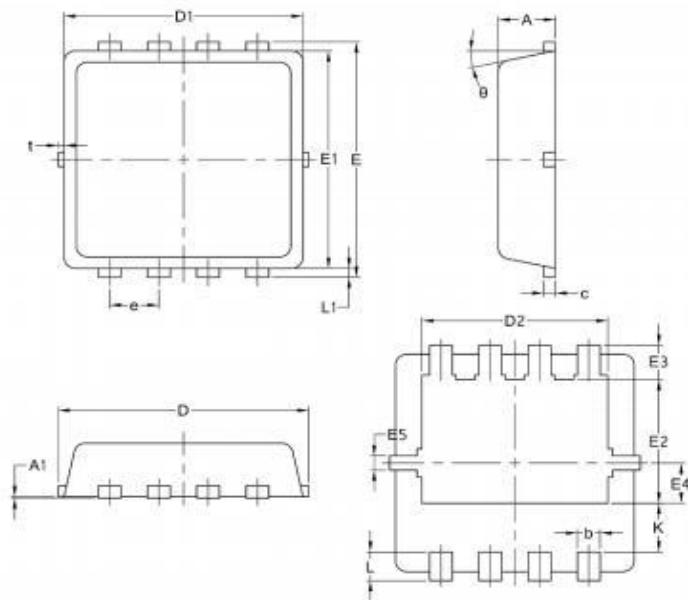


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

**Package Mechanical Data-PDFN3\*3-8L-JQ Single**

Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14

**Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN3*3-8L		5000